NSN 5961-01-123-2989

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-123-2989 **Inclosure Material:** Glass **Overall Length:** 0.300 inches **Terminal Length:** 1.000 inches **Overall Diameter:** 0.130 inches **End Application:** Blank system 76301 **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 3.0 regulator voltage **Current Rating Per Characteristic:** 4.00 microamperes forward current, average peak **Power Rating Per Characteristic:** 400.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Special Features:** Cnuclear hardness critical item; no drawing to determine if isc code 1 item should be nuclear hardness. Can't change criticality code to reflect nuclear hardness; junciton pattern arrangement: pin **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/435 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Fiig: A110a0

No